

Monolithic Amplifier

PGA-122-75+

75Ω 5 to 1500 MHz

THE BIG DEAL

- · High IP3, 43 dBm typ. at 0.5 GHz
- Gain, 15.6 dB typ. at 0.5 GHz
- High Pout, P1dB 73.1 dBmV typ. at 0.5 GHz
- Low Noise Figure, 2.9 dB at 0.5 GHz
- Usable over 5-2000 MHz



Generic photo used for illustration purposes only

CASE STYLE: DF782

+RoHS Compliant

The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

APPLICATIONS

- CATV, DOCSIS 3.1
- GPON
- MOCA
- DBS

PRODUCT OVERVIEW

PGA-122-75+ (RoHS compliant) is an advanced wideband amplifier fabricated using E-PHEMT technology and offers extremely high dynamic range over a broad frequency range with low noise figure and flat gain. Lead finish is SnAgNi. It has repeatable performance from lot to lot and is enclosed in a SOT-89 package for very good thermal performance.

KEY FEATURES

Feature	Advantages	
Broad Band: 0.04 to 1.5 GHz	0.04 to 1.5 GHz bandwidth covers primary CATV applications such as DOCSIS 3.1	
Application circuit for 5 to 2000 MHz available	Supports bandwidth requirements for upstream CATV applications. See application note AN-60-087. Recommend Evaluation Board, TB-885+	
High IP3 Versus DC power Consumption: 43 dBm typical at 0.5 GHz	The PGA-122-75+ matches industry leading IP3 performance relative to device size and power consumption. The combination of the design and E-PHEMPT structure provides enhanced linearity over a broad frequency range as evidence in the IP3 being typically 15-20 dB above the P 1dB point. This feature makes this amplifier ideal for use in CATV applications.	
High IP2, 54 dBm at 0.5 GHz	Suppresses second order product on wideband applications such as CATV	
Low Noise Figure, 2.9 dB at 0.5 GHz	Low noise figure performance in combination with the high output IP3 results in high dynamic range.	
Excellent CSO/CTB* CSO, -59 dBc CTB, -80 dBc Measured at channel 78	Competitive performance at lower current and supply voltage.	

^{*78} channels flat, 30 dBmv/channel at output, 6 MHz channel spacing.

REV. A ECO-011959 PGA-122-75+ TH/RS/CP 220216





Monolithic Amplifier PGA-122-75+

ELECTRICAL SPECIFICATIONS AT 25°C, 75Ω AND 9V¹ UNLESS NOTED OTHERWISE

Dawanatan	Condition	Vd=9V		Vd=8V	Units	
Parameter	(GHz)	Min.	Тур.	Max.	Тур.	Units
Frequency range		0.04		1.5	0.04-1.5	GHz
	0.04	_	15.5	_	15.5	
	0.5	_	15.6	_	15.6	
Gain	1.0	14.0	15.5	17.1	15.5	dB
	1.25	_	15.4	_	15.3	
	1.5	_	15.1	_	15.0	
Gain flatness over	0.04-1.25		±0.1		±0.1	dB
	0.04		17.8		17.6	
	0.5		21.2		20.8	
Input return loss	1.0		18.7		18.0	dB
	1.25		16.1		15.9	
	1.5		14.2		13.8	
	0.04		19.8		20.2	
	0.5		24.3		24.1	
Output return loss	1.0		16.4		16.7	dB
	1.25		13.0		13.0	
	1.5		10.0		9.8	
Reverse isolation	1.0		21.0		21.0	dB
	0.04		23.4 (72.2)		22.4 (71.2)	
	0.5		24.3 (73.1)		23.3 (72.1)	dBm
Output power @1dB compression	1.0		23.8 (72.6)		23.1 (71.9)	(dBmV)
	1.25		23.3 (72.1)		22.3 (71.1)	
	1.5		22.8 (71.6)		21.6 (70.4)	
	0.04		43.3		42.3	
	0.5		43.2		43.6	
Output IP3	1.0		41.4		39.9	dBm
	1.25		38.8		37.0	
	1.5		37.9		35.4	
	0.04		59.5		56.9	
	0.5		54.9		53.0	
Output IP2 ²	1.0		58.5		57.5	dBm
	1.25		52.2		50.1	
	1.5		49.4		47.2	
	0.04		2.9		3.0	
	0.5		2.9		2.8	
Noise figure	1.0		2.8		2.9	dB
	1.25		3.0		2.9	
	1.5		3.0		3.2	
Device operating voltage		8.5	9.0	9.5	8.0	V
Device operating current		_	115	140	102	mA
Device current variation vs temperature ⁴			22		25	μA°/C
Device current variation vs voltage			0.0146		0.0146	mA/mV
Thermal resistance, junction-to-ground lead ³			30		30	°C/W

^{1.} Measured on Mini-Circuits Characterization Eval board TB-859+. See Characterization Test Circuit (Fig. 1)

MAXIMUM RATINGS⁵

III Daniel III II I			
Parameter	Ratings		
Operating Temperature (ground lead)	-40°C to 85°C		
Storage Temperature	-65°C to 150°C		
Operating Current at 9.0V	167 mA		
Power Dissipation	1.5 W		
Input Power (CW)	+20 dBm over 40-1200 MHz, and +24 dBm over 1200-1500 MHz (5 minutes) +17 dBm over 40-1200 MHz, and +20 dBm over 1200-1500 MHz (continuous)		
DC Voltage on Pin 3	11 V		

^{5.} Permanent damage may occur if any of these limits are exceeded. Electrical maximum ratings are not intended for continuous normal operation.

Mini-Circuits

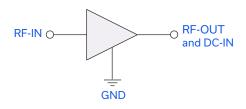
^{2.} Output IP2 measured at sum frequency of the two tones (f meas= f1+f2).

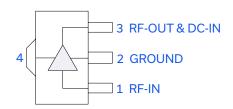
^{3.} Junction to ground lead. 4. (Current at 85°C - Current at -45°C)/130



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SIMPLIFIED SCHEMATIC AND PIN DESCRIPTION





Function	Pin Number	Description	
RF-IN	1	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.	
RF-OUT and DC-IN	3	RF output and bias pin. DC voltage is present on this pin; therefore a DC blocking capacitor is necessary for proper operation. An RF choke is needed to feed DC bias without loss of RF signal due to the bias connection, as shown in "Recommended Application Circuit", Fig. 2	
GND	2,4	Connections to ground. Use via holes as shown in "Suggested Layout for PCB Design" to reduce ground path inductance for best performance.	

^{*}Enhanced mode pseudomorhic High Electron Mobility Transistor.

Monolithic Amplifier PGA-122-75+

CHARACTERIZATION TEST CIRCUIT

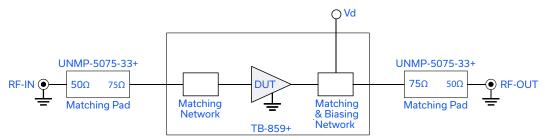


Fig 1. Block Diagram of Test Circuit used for characterization. (DUT tested on Mini-Circuits Characterization Eval board TB-859+) Gain, Return loss, Output power at 1dB compression (P1 dB), output IP3 (OIP3), output IP2 (OIP2) and noise figure measured using Agilent's N5242A PNA-X microwave network analyzer.

Conditions:

- 1. Gain and Return loss: Pin= -25dBm
- 2. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, 5 dBm/tone at output.
- 3. Output IP2 (OIP2): Two tones, spaced 11 MHz apart, 5 dBm/tone at output.

RECOMMENDED APPLICATION CIRCUIT (TB-850+)

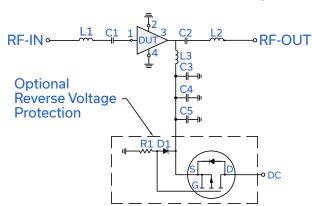


Fig 2. Evaluation board includes case, connectors, and components soldered to PCB
Note: R1, D3 and Q1 are for reverse voltage protection and may be ommited.

COMPONENT	VALUE	SIZE	
DUT	PGA-122-75+	-	
C1	1000 pF		
C2	120 pF	0402	
C3	100 pF	0.02	
C4	10000 pF		
C5	10 uF, 25V	1206	
D1	Zener Diode 5.6V ONSEMI MMSZ4690T1G	SOD123	
L1	3.3 nH	0402	
L2	4.7 nH	0402	
L3	560 nH	0603	
R1	1.5 k0hm		
Q1	Transistor ONSEMI FET NTS4101P	S0T323	

PRODUCT MARKING



Marking may contain other features or characters for internal lot control



Monolithic Amplifier PGA-122-75+

ADDITIONAL DETAILED TECHNICAL INFORMATION IS AVAILABLE ON OUR DASH BOARD. TO ACCESS CLICK HERE

	Data Table
Performance Data	Swept Graphs
	S-Parameter (S2P Files) Data Set (.zip file)
5-200 MHz Operation	See Application Note AN-60-087
Case Style	DF782 (SOT 89) Plastic package, exposed paddle lead finish: tin-silver over nickel
Tape & Reel Standard quantities available on reel	F477
Suggested Layout for PCB Design	PL-477
Evaluation Board	TB-850+ (40-1500 MHz) TB-885+ (5-20 MHz)
Environmental Ratings	ENV08T1

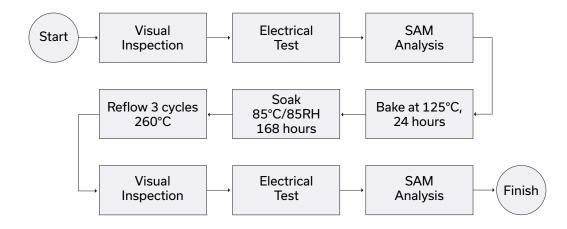
ESD RATING

Human Body Model (HBM): Class 1A (250<500) in accordance with ANSI/ESD STM 5.1 - 2001 Machine Model (MM): Class class M1 (25V) in accordance with ANSI/ESD STM5.2-1999

MSL RATING

Moisture Sensitivity: MSL1 in accordance with IPC/JEDEC J-STD-020D

MSL TEST FLOW CHART



- A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.
- B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.
- C. The parts covered by this specification document are subject to Mini-Circuits standard limited warranty and terms and conditions (collectively, "Standard Terms"); Purchasers of this part are entitled to the rights and benefits contained therein. For a full statement of the standard. Terms and the exclusive rights and remedies thereunder, please visit Mini-Circuits' website at www.minicircuits.com/MCLStore/terms.jsp